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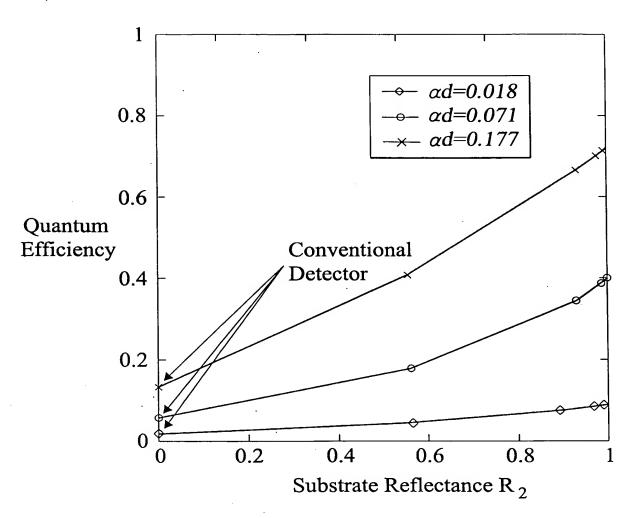


FIG. I

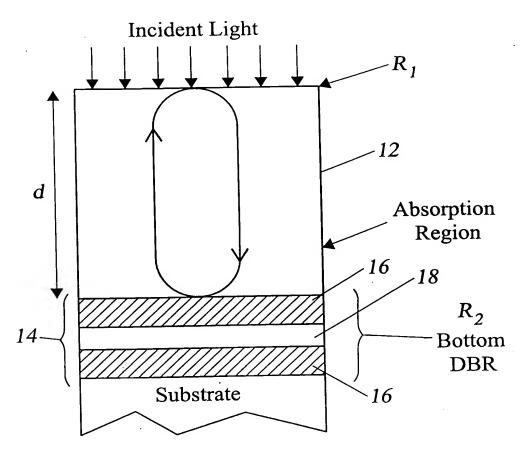


FIG. 2

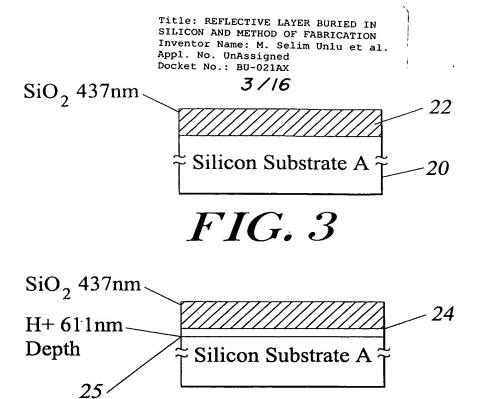
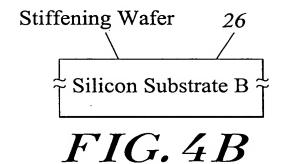
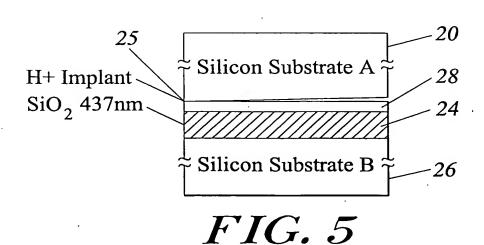
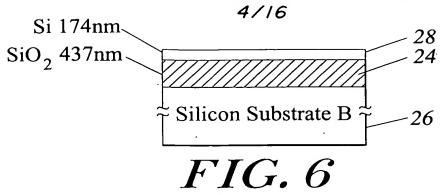


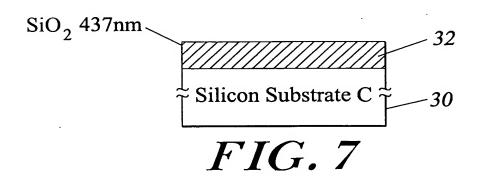
FIG. 4A

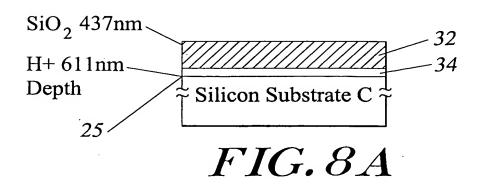


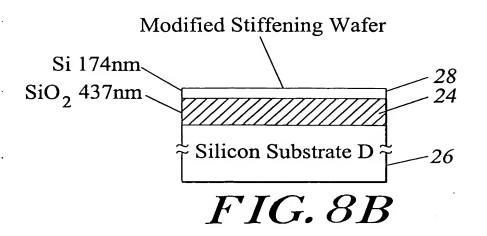


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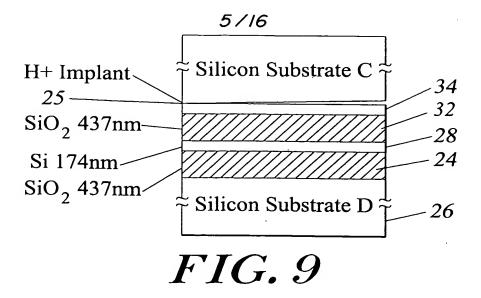


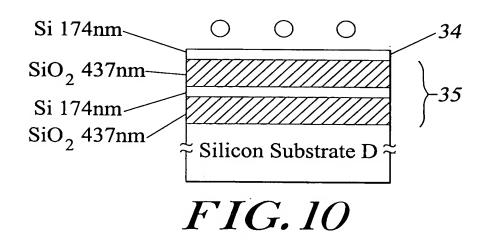


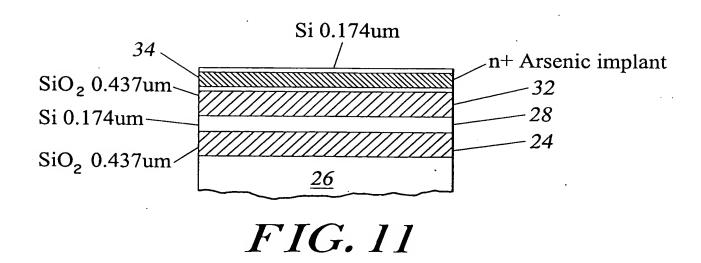


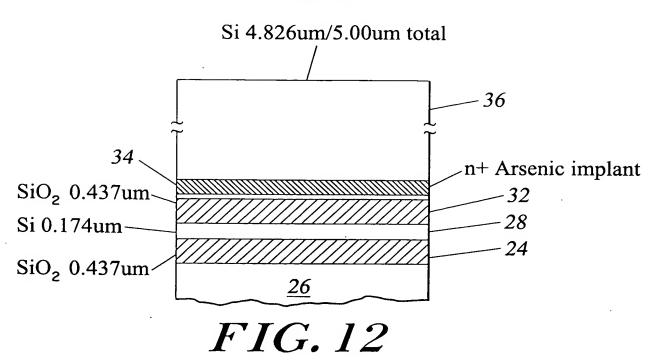


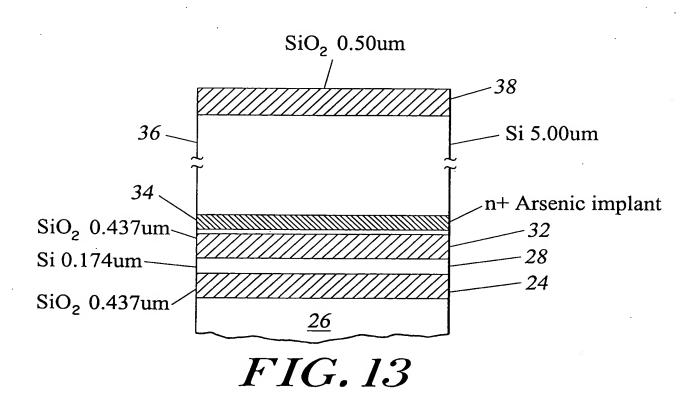
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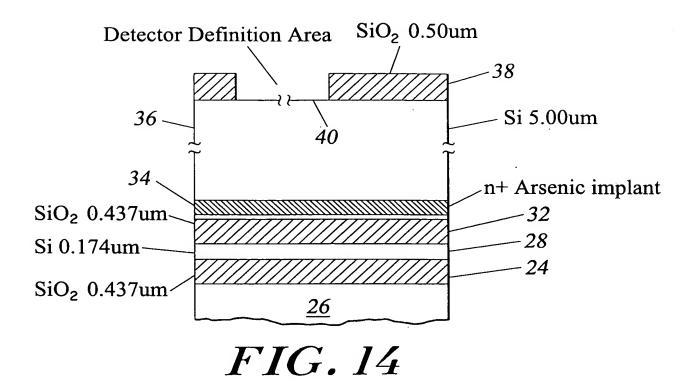


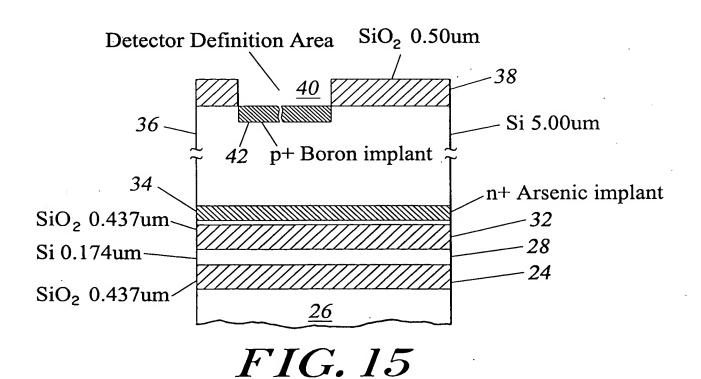


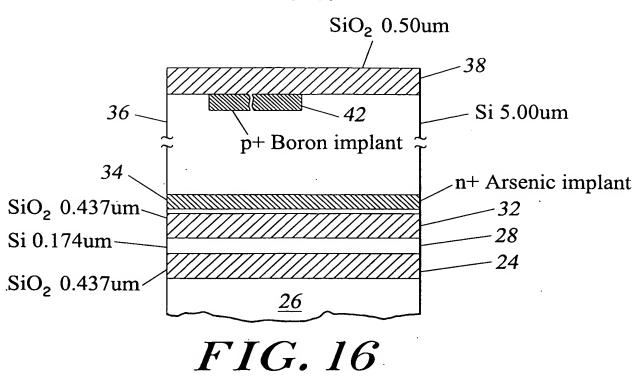


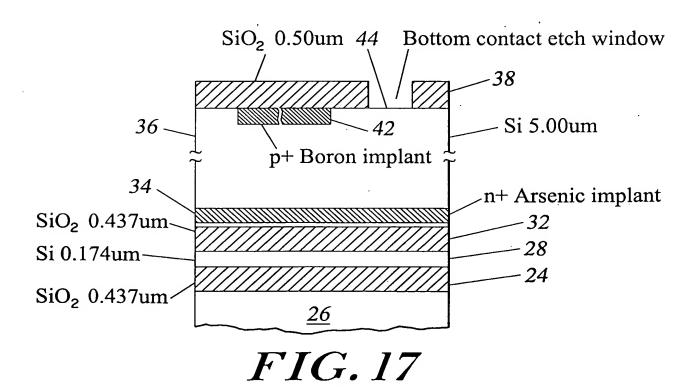


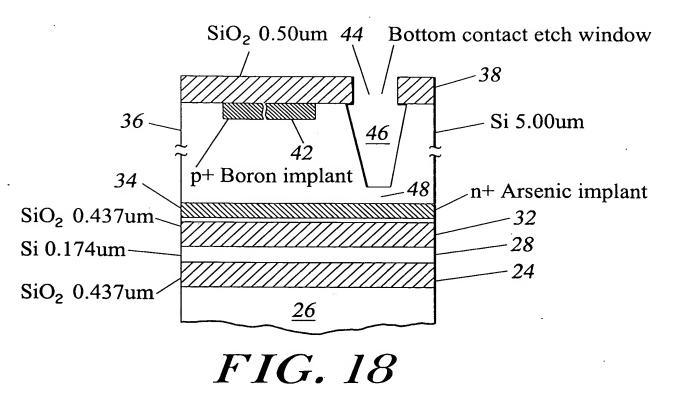


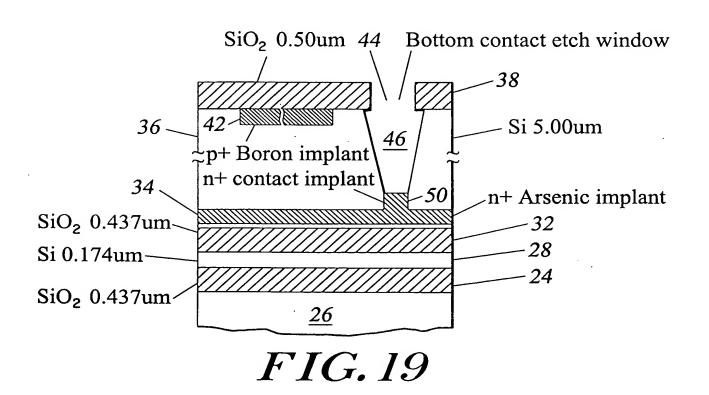


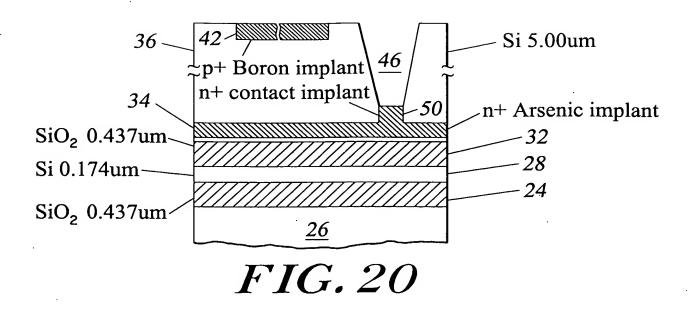


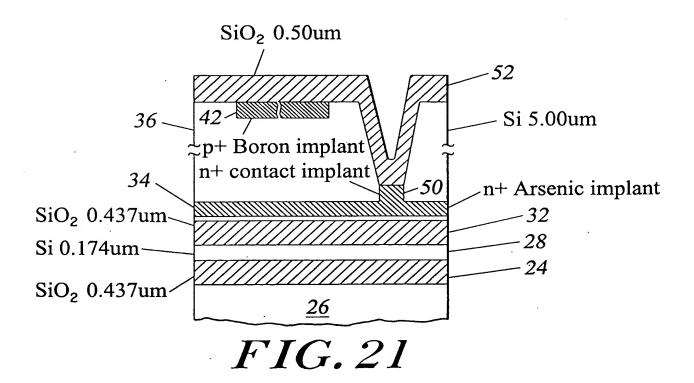


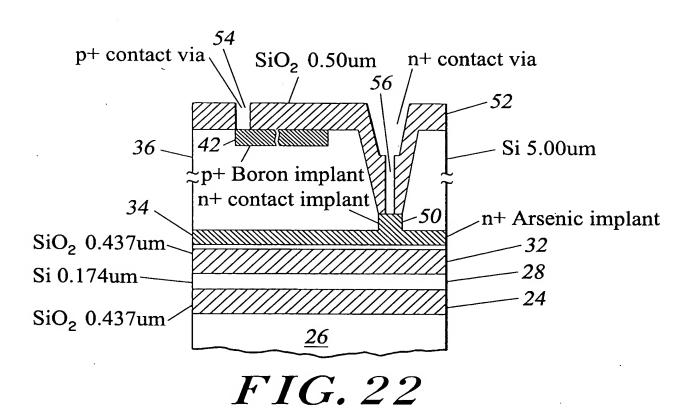


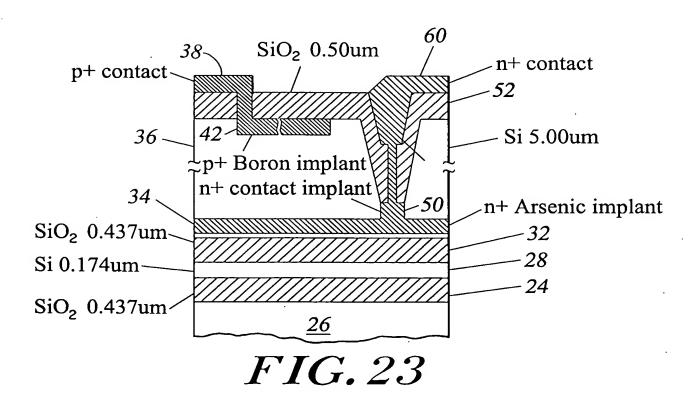


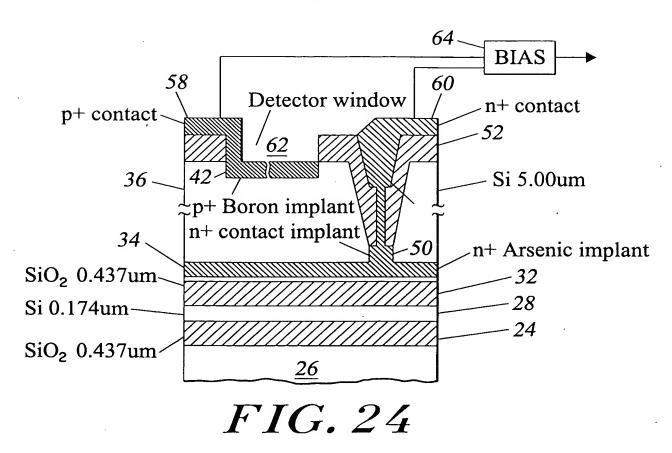


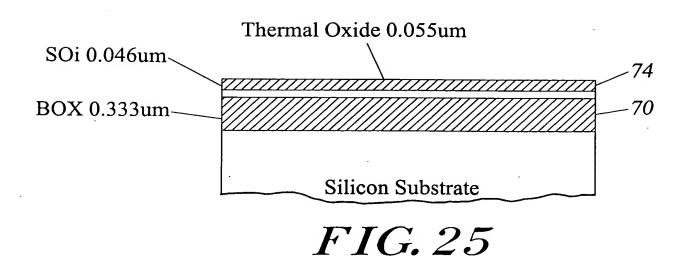




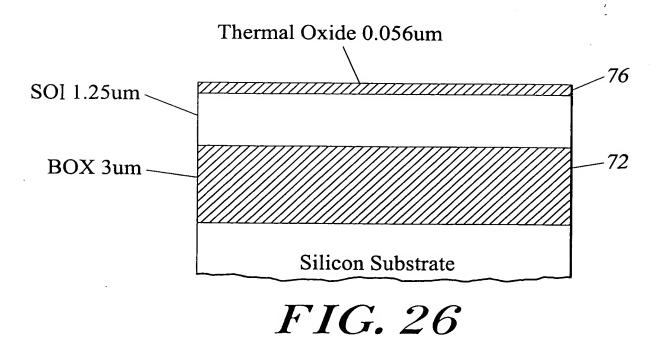


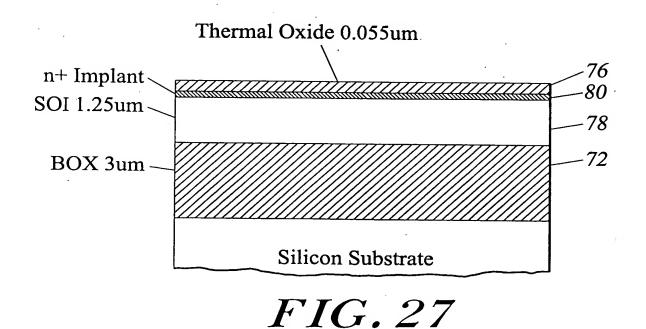




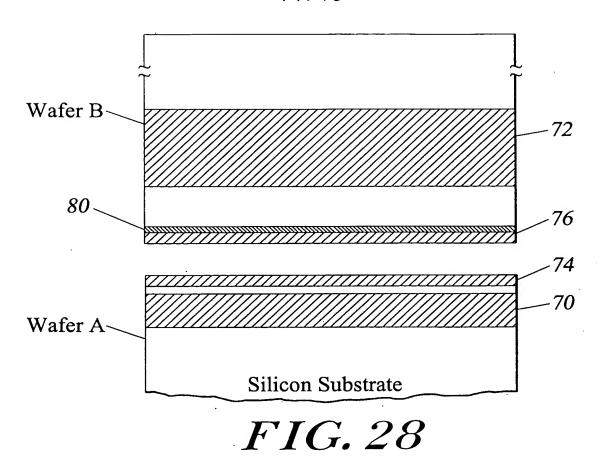


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Thin Silicon Layer

Top Oxide

Si 1.25um
n+ region
SiO<sub>2</sub> 0.111um
Si 0.046um
SiO<sub>2</sub> 0.333um

Silicon Substrate

FIG. 29

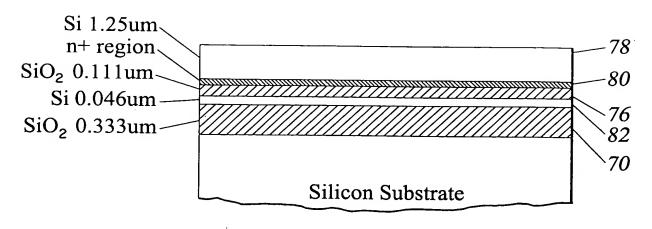


FIG. 30

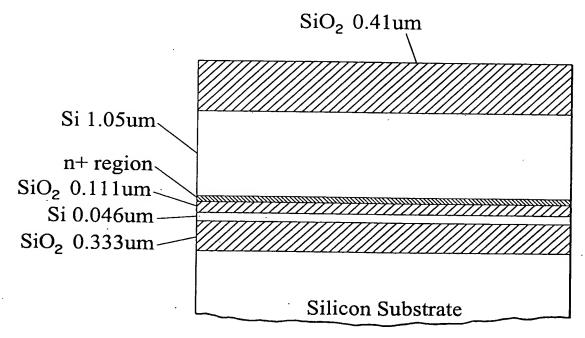


FIG. 31

Title: REFLECTIVE LAYER BURIED IN SILICON AND METHOD OF FABRICATION Inventor Name: M. Selim Unlu et al.

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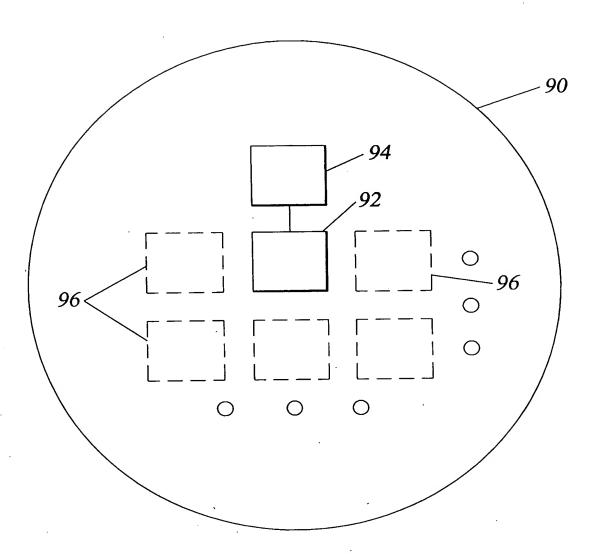


FIG. 32